

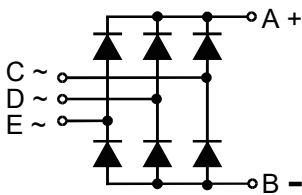
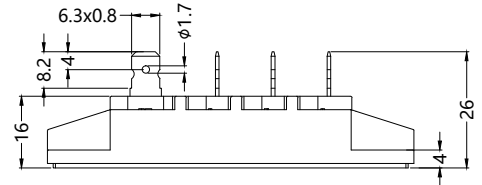
S3PDB30N16


Three Phase Rectifier Modules

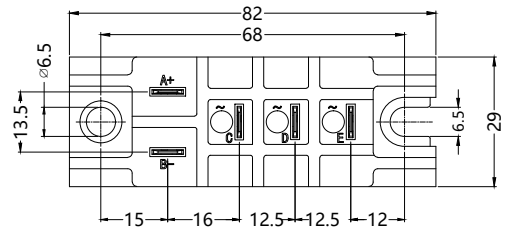
Dimensions in mm (1mm=0.0394")



Type	V _{RSM} V	V _{RRM} V
S3PDB30N08	900	800
S3PDB30N12	1300	1200
S3PDB30N14	1500	1400
S3PDB30N16	1700	1600
S3PDB30N18	1900	1800



 E310749



Symbol	Test Conditions	Maximum Ratings	Unit
I _{dav}	T _C =100°C, module	30	A
I _{FSM}	T _{VJ} =45°C t=10ms (50Hz), sine V _R =0 t=8.3ms (60Hz), sine	270 300	A
	T _{VJ} =T _{VJM} t=10ms(50Hz), sine V _R =0 t=8.3ms(60Hz), sine	230 255	
I ² t	T _{VJ} =45°C t=10ms (50Hz), sine V _R =0 t=8.3ms (60Hz), sine	450 460	A ² s
	T _{VJ} =T _{VJM} t=10ms(50Hz), sine V _R =0 t=8.3ms(60Hz), sine	350 33	
T _{VJ} T _{VJM} T _{stg}		-40...+150 150 -40...+125	°C
V _{ISOL}	50/60Hz, RMS t=1min I _{ISOL} ≤1mA t=1s	2500 3000	V~
M _d	Mounting torque (M6)	4.7	Nm
Weight	typical	92	g

Sirectifier[®]

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Symbol	Test Conditions	Characteristic Values	Unit
I_R	$V_R=V_{RRM}; T_{VJ}=25^{\circ}C$ $V_R=V_{RRM}; T_{VJ}=T_{VJM}$	≤ 0.3 ≤ 5	mA
V_F	$I_F=30A; T_{VJ}=25^{\circ}C$	≤ 1.20	V
V_{TO}	For power-loss calculations only	0.8	V
r_T		40	m Ω
R_{thJC}	per diode; per module	0.9 0.15	K/W
R_{thJH}	per diode; per module	1.1 0.57	K/W
d_s	Creeping distance on surface	16.1	mm
d_A	Creepage distance in air	7.5	mm
a	Max. allowable acceleration	50	m/s ²

FEATURES

- * Package with copper base plate
- * Isolation voltage 3000 V~
- * Glass passivated chips
- * 1/4" fast-on power terminal
- * Low forward voltage drop
- * UL File NO.E310749
- * RoHS compliant

APPLICATIONS

- * Supplies for DC Power equipment
- * Input rectifier for PWM inverter
- * Battery DC power supplies
- * Field supply for DC motors

ADVANTAGES

- * Easy to mount with two screws
- * Space and weight savings
- * Improved temperature and power cycling

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